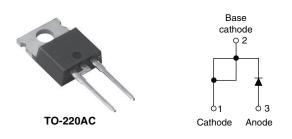
VS-15ETU12HN3

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Ultrafast Rectifier, 15 A FRED Pt[®]



PRODUCT SUMMARY								
Package	TO-220AC							
I _{F(AV)}	15 A							
V _R	1200 V							
V _F at I _F at 125 °C	2.25 V							
t _{rr}	44 ns							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and soft recovery time
- Optimized forward voltage drop
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Rugged design
- Good thermal performance
- AEC-Q101 qualified
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, recovery time, and soft recovery. Polyimide passivated, planar structure and the platinum doped life time control guarantee, ruggedness, reliability characteristics, and solid value proposition for efficiency and thermal performance.

These devices are intended for use in boost stage in the AC/DC section of SMPS, high frequency output rectification of battery charger, inverters of solar inverters, or as freewheeling diodes in motor drive.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	T _C = 115 °C, D = 0.50	15							
Non-repetitive peak surge current	I _{FSM}	$T_C = 25 \text{ °C}, t_p = 10 \text{ ms}, \text{ sine wave}$	150	А						
Repetitive peak forward current	I _{FRM}		30							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL TEST CONDITIONS				MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 250 μA	1200	-	-					
Forward voltage	V _F	I _F = 15 A	-	2.3	2.78	V				
		I _F = 15 A, T _J = 125 °C	-	2.25	2.7					
Povereo lookago ourrent	I _R	$V_R = V_R$ rated	-	-	80					
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	150	μA				
Junction capacitance	CT	V _R = 200 V	-	13	-	pF				
Series inductance	Ls	Measured lead to lead 5 mm from package body	-	8.0	-	nH				

 Revision: 31-May-16
 1
 Document Number: 95645

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RoHS

COMPLIANT HALOGEN

FREE



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1.0 \text{ A}, \text{ d}_F/\text{d}t = 10$	00 A/µs, V _R = 30 V	-	44	-				
Reverse recovery time	t _{rr}	T _J = 25 °C		-	167	-	ns			
		T _J = 125 °C		-	248	-				
Pools recovery ourrent	I	$T_J = 25 \ ^\circ C$	$I_F = 15 A$	-	6	-	A			
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 100 A/µs V _B = 390 V	-	9	-				
	Q _{rr}	T _J = 25 °C		-	507	-	nC			
Reverse recovery charge		T _J = 125 °C		-	1110	-				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction to case	R _{thJC}		-	1.1	1.3					
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	54	60	°C/W				
Thermal resistance, case to heat sink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	0.4					
Maiabt			-	0.2	-	g				
Weight			-	0.07	-	oz.				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style: TO-220AC		15ET	U12H					

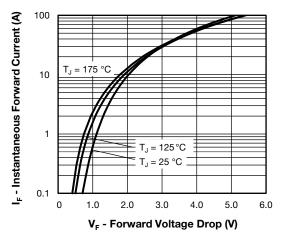


Fig. 1 - Typical Forward Voltage Drop Characteristics

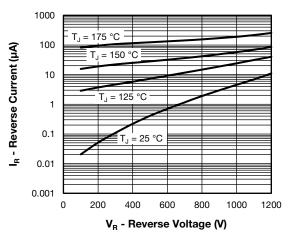


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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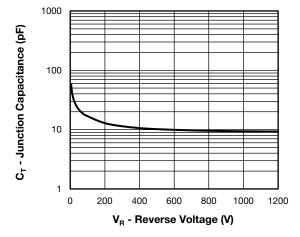


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

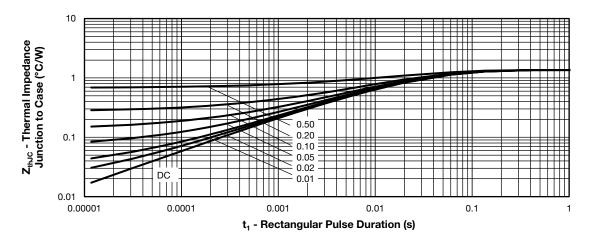


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

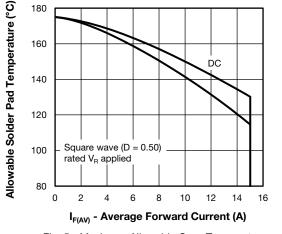


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

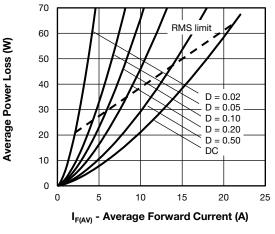


Fig. 6 - Forward Power Loss Characteristics

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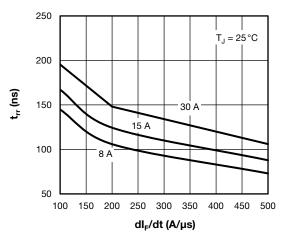
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

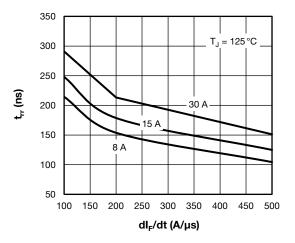


Fig. 8 - Typical Reverse Recovery Time vs. dI_F/dt

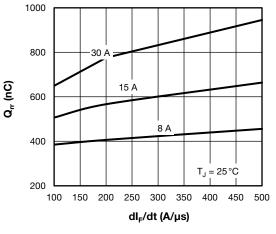


Fig. 9 - Typical Stored Charge vs. dl_F/dt

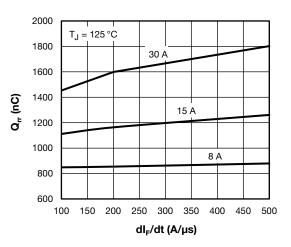
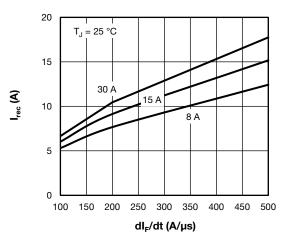


Fig. 10 - Typical Stored Charge vs. dl_F/dt





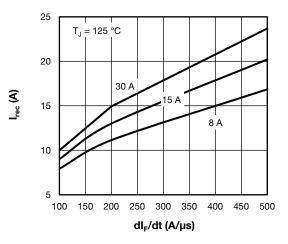


Fig. 12 - Typical Reverse Current vs. dl_F/dt

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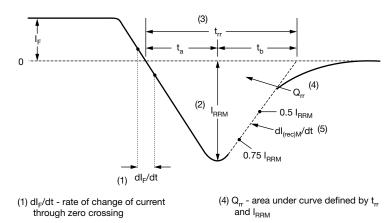
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(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current. $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 13 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code

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ode	vs-		15	Е	т	U	12	н	N3
		(2)	(3)	(4)	(5)	(6)	(7)	(8)
	1	_	Visł	nay Sen	niconduo	ctors pro	oduct	0	C
	2	-	Cur	rent rati	ng (15 =	= 15 A)			
	3	-	E =	single o	liode				
	4	-	Pac	kage:					
			T =	TO-220					
	5	-	U =	ultrafas	t recove	ery			
	6	-	Volt	age rati	ng (12 =	= 1200 \	/)		
	7	-	H =	AEC-Q	101 qua	lified			
	8	-	Env	rironmer	ntal digit	:			
			-N3	= halog	en-free	RoHS-	complia	nt, and	totally I

ORDERING INFORMATI	ON (Example)		
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-15ETU12HN3	50	1000	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95221						
Part marking information	www.vishay.com/doc?95068						

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TO-220AC

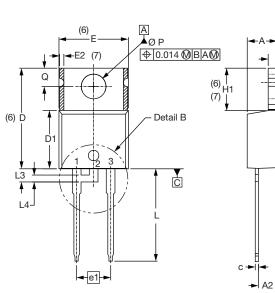
B Seating

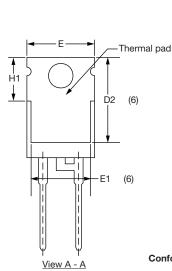
A-

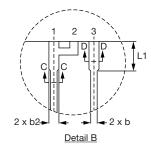
-A1

plane

DIMENSIONS in millimeters and inches









Conforms to JEDEC[®] outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NULES
А	4.25	4.65	0.167	0.183		E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055		E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115		e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040		H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4	L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068		L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4	L3	1.78	2.13	0.070	0.084	
с	0.36	0.61	0.014	0.024		L4	0.76	1.27	0.030	0.050	2
c1	0.36	0.56	0.014	0.022	4	ØР	3.54	3.73	0.139	0.147	
D	14.85	15.25	0.585	0.600	3	Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355							
D2	11.68	12.88	0.460	0.507	6						
E	10.11	10.51	0.398	0.414	3, 6						

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

(2) Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- (4) Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1

⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed

⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

Revision: 09-Sep-2019

Document Number: 95221



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